

Low-voltage stabistors**BZV86 series****FEATURES**

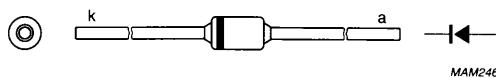
- Low-voltage stabilization
- Forward voltage range: 1.4 to 3.2 V
- Total power dissipation:
max. 330 mW
- Differential resistance range:
max. 20 to 35 Ω .

APPLICATIONS

- Power clipping
- Level shifting
- Low-voltage regulation
- Temperature stabilization.

DESCRIPTION

Low-voltage stabilization diode in a hermetically-sealed SOD27 (DO-35) glass package. The series consists of four types: BZV86-1V4 to BZV86-3V2.



The diodes are type branded.

Fig.1 Simplified outline (SOD27; DO-35) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_R	continuous reverse voltage		–	10	V
I_F	continuous forward current BZV86-1V4 BZV86-2V0 BZV86-2V6 BZV86-3V2		– – – –	200 150 125 100	mA mA mA mA
P_{tot}	total power dissipation	$T_{amb} = 25^\circ\text{C}$	–	330	mW
T_{stg}	storage temperature		–65	+150	$^\circ\text{C}$
T_j	junction temperature		–	150	$^\circ\text{C}$

Low-voltage stabistors

BZV86 series

ELECTRICAL CHARACTERISTICS

 $T_j = 25^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_F	forward voltage BZV86-1V4	$I_F = 5 \text{ mA}; \text{ see Fig.2}$	1.30	—	1.50	V
	BZV86-2V0		1.85	—	2.15	V
	BZV86-2V6		2.35	—	2.80	V
	BZV86-3V2		2.85	—	3.45	V
I_R	reverse current	$V_R = 5 \text{ V}$	—	—	200	nA
r_{dif}	differential resistance BZV86-1V4	$I_F = 1 \text{ mA}; f = 1 \text{ kHz}$	—	55	—	Ω
	BZV86-2V0		—	80	—	Ω
	BZV86-2V6		—	90	—	Ω
	BZV86-3V2		—	100	—	Ω
r_{dif}	differential resistance BZV86-1V4	$I_F = 5 \text{ mA}; f = 1 \text{ kHz}$	—	10	20	Ω
	BZV86-2V0		—	15	30	Ω
	BZV86-2V6		—	18	32.5	Ω
	BZV86-3V2		—	20	35	Ω
r_{dif}	differential resistance BZV86-1V4	$I_F = 10 \text{ mA}; f = 1 \text{ kHz}$	—	6	10	Ω
	BZV86-2V0		—	8	15	Ω
	BZV86-2V6		—	9	17.5	Ω
	BZV86-3V2		—	10	20	Ω
S_F	temperature coefficient BZV86-1V4	$I_F = 5 \text{ mA}$	—	-3.8	—	mV/K
	BZV86-2V0		—	-6.0	—	mV/K
	BZV86-2V6		—	-8.5	—	mV/K
	BZV86-3V2		—	-11.5	—	mV/K
C_d	diode capacitance	$V_R = 0 \text{ V}; f = 1 \text{ MHz}$	—	15	25	pF

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th j\text{-tp}}$	thermal resistance from junction to tie-point	8 mm from the body	300	K/W
$R_{th j\text{-a}}$	thermal resistance from junction to ambient	lead length 10 mm	380	K/W